

Small Signal Fast Switching Diodes



FEATURES

- Silicon epitaxial planar diode
- Electrical data identical with the devices 1N4148 and 1N4448 respectively
- AEC-Q101 qualified



RoHS
COMPLIANT

APPLICATIONS

- Extreme fast switches

MECHANICAL DATA

Case: MiniMELF SOD-80

Weight: approx. 31 mg

Cathode band color: black

Packaging codes/options:

GS18/10K per 13" reel (8 mm tape), 10K/box

GS08/2.5K per 7" reel (8 mm tape), 12.5K/box

PARTS TABLE					
PART	TYPE DIFFERENTIATION	ORDERING CODE	TYPE MARKING	INTERNAL CONSTRUCTION	REMARKS
LL4148	$V_{RRM} = 100\text{ V}$, $V_F = \text{max. } 1000\text{ mV at } I_F = 50\text{ mA}$	LL4148-GS08 or LL4148-GS18	-	Single diode	Tape and reel
LL4448	$V_{RRM} = 100\text{ V}$, $V_F = \text{max. } 1000\text{ mV at } I_F = 100\text{ mA}$	LL4448-GS08 or LL4448-GS18	-	Single diode	Tape and reel

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^\circ\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Repetitive peak reverse voltage		V_{RRM}	100	V
Reverse voltage		V_R	75	V
Peak forward surge current	$t_p = 1\text{ }\mu\text{s}$	I_{FSM}	2	A
Repetitive peak forward current		I_{FRM}	500	mA
Forward continuous current		I_F	300	mA
Average forward current	$V_R = 0$	$I_{F(AV)}$	150	mA
Power dissipation ⁽¹⁾		P_{tot}	500	mW

Note

⁽¹⁾ Valid provided that electrodes are kept at ambient temperature

THERMAL CHARACTERISTICS ($T_{amb} = 25\text{ }^\circ\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Thermal resistance junction to ambient air ⁽¹⁾		R_{thJA}	300	K/W
Junction temperature		T_J	175	$^\circ\text{C}$
Storage temperature range		T_{stg}	- 65 to + 175	$^\circ\text{C}$

Note

⁽¹⁾ Valid provided that electrodes are kept at ambient temperature

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 5\text{ mA}$	LL4448	V_F	620		720	mV
	$I_F = 50\text{ mA}$	LL4148	V_F		860	1000	mV
	$I_F = 100\text{ mA}$	LL4448	V_F		930	1000	mV
Reverse current	$V_R = 20\text{ V}$		I_R			25	nA
	$V_R = 20\text{ V}, T_j = 150\text{ }^{\circ}\text{C}$		I_R			50	μA
	$V_R = 75\text{ V}$		I_R			5	μA
Breakdown voltage	$I_R = 100\text{ }\mu\text{A}, t_p/T = 0.01,$ $t_p = 0.3\text{ ms}$		$V_{(BR)}$	100			V
Diode capacitance	$V_R = 0\text{ V}, f = 1\text{ MHz},$ $V_{HF} = 50\text{ mV}$		C_D			4	pF
Reverse recovery time	$I_F = I_R = 10\text{ mA},$ $i_R = 1\text{ mA}$		t_{rr}			8	ns
	$I_F = 10\text{ mA}, V_R = 6\text{ V},$ $i_R = 0.1 \times I_R, R_L = 100\text{ }\Omega$					4	

TYPICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

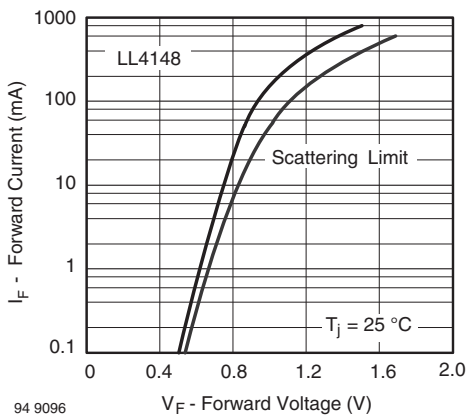


Fig. 1 - Forward Current vs. Forward Voltage

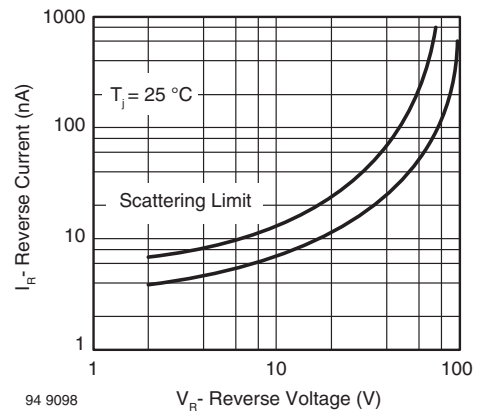


Fig. 3 - Reverse Current vs. Reverse Voltage

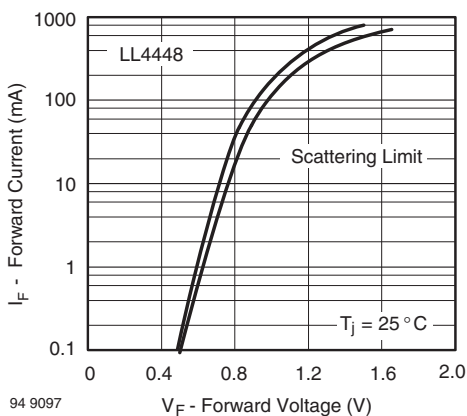


Fig. 2 - Forward Current vs. Forward Voltage

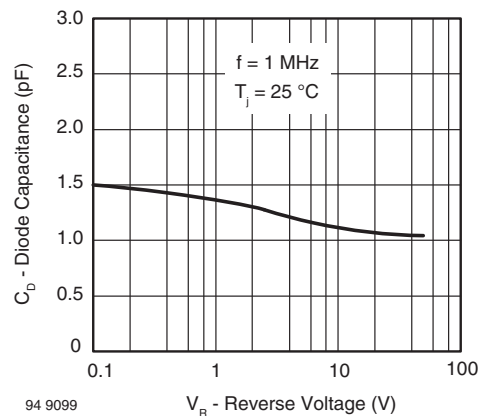
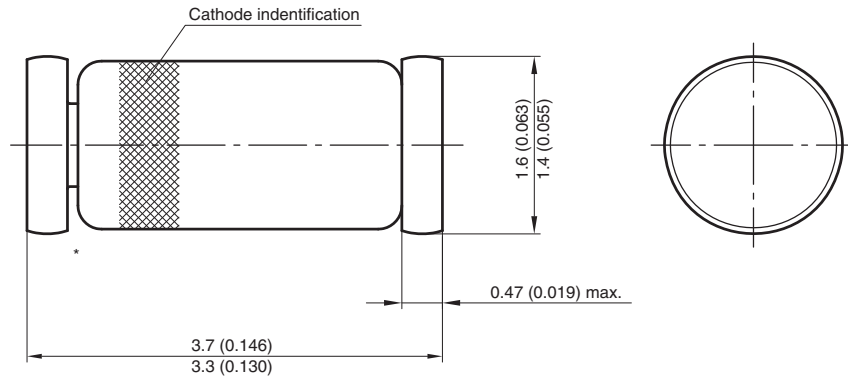
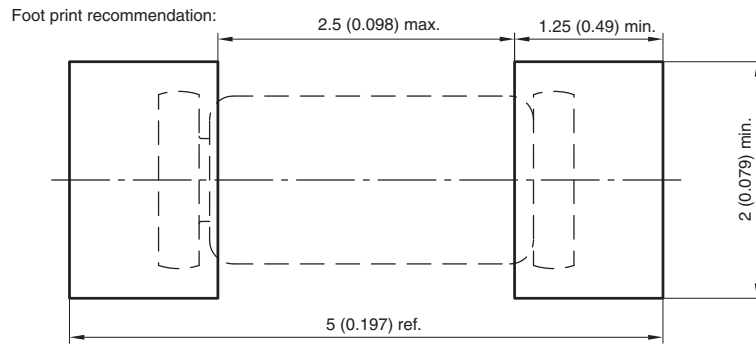


Fig. 4 - Diode Capacitance vs. Reverse Voltage

PACKAGE DIMENSIONS in millimeters (inches): **MiniMELF SOD-80**



* The gap between plug and glass can be either on cathode or anode side



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